

BB303M

Build in Biasing Circuit MOS FET IC
VHF/UHF RF Amplifier

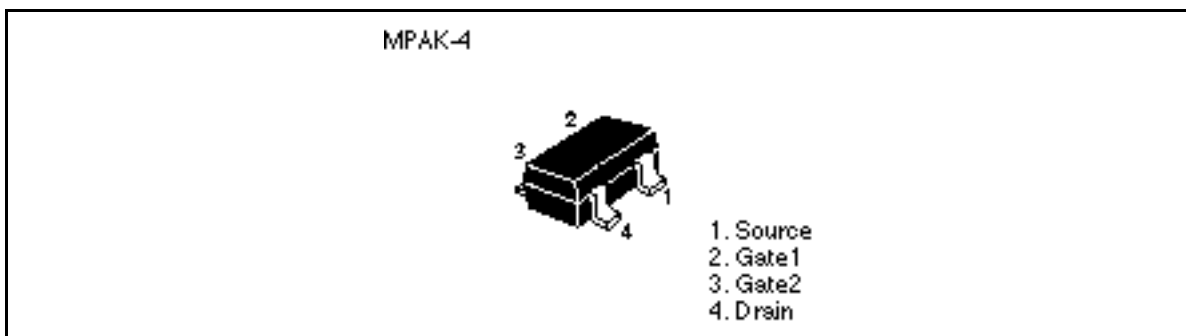
HITACHI

ADE-208-697A (Z)
2nd. Edition
Nov. 1998

Features

- Σ Build in Biasing Circuit; To reduce using parts cost & PC board space.
- Σ High forward transfer admittance;
($|y_{fs}| = 42 \text{ mS typ. at } f = 1 \text{ kHz}$)
- Σ Withstanding to ESD;
Build in ESD absorbing diode. Withstand up to 250V at $C=200\text{pF}$, $R_s=0$ conditions.
- Σ Provide mini mold packages; MPAK-4 (SOT-143 var.)

Outline



- Notes: 1. Marking is "CW-".
2. BB303M is individual type number of HITACHI BBFET.

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

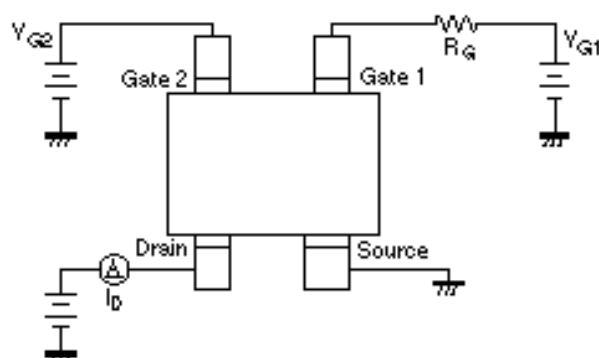
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	7	V
Gate1 to source voltage	V_{G1S}	- 0/ +7	V
Gate2 to source voltage	V_{G2S}	- 0/ +7	V
Drain current	I_D	25	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	$^\circ\text{C}$
Storage temperature	Tstg	-55 to +150	$^\circ\text{C}$

BB303M

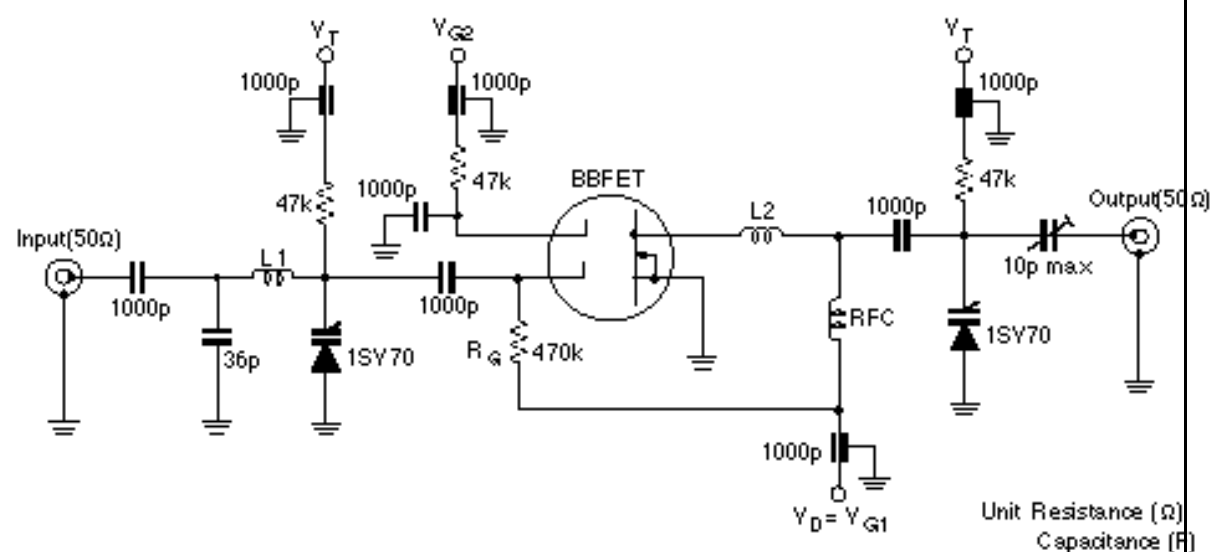
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	7	—	—	V	$I_D = 200mA$ $V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+7	—	—	V	$I_{G1} = +10mA$ $V_{G2S} = V_{DS} = 0$
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	+7	—	—	V	$I_{G2} = +10mA$ $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff current	I_{G1SS}	—	—	+100	nA	$V_{G1S} = +5V$ $V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	I_{G2SS}	—	—	+100	nA	$V_{G2S} = +5V$ $V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.3	0.6	0.9	V	$V_{DS} = 5V, V_{G2S} = 4V$ $I_D = 100mA$
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.5	0.8	1.1	V	$V_{DS} = 5V, V_{G1S} = 5V$ $I_D = 100mA$
Drain current	$I_{D(op)}$	9	14	20	mA	$V_{DS} = 5V, V_{G1} = 5V$ $V_{G2S} = 4V, R_G = 470kW$
Forward transfer admittance	$ y_{fs} $	35	42	50	mS	$V_{DS} = 5V, V_{G1} = 5V$ $V_{G2S} = 4V$ $R_G = 470kW, f = 1kHz$
Input capacitance	C_{iss}	2.6	3.3	4.0	pF	$V_{DS} = 5V, V_{G1} = 5V$
Output capacitance	C_{oss}	1.7	2.1	2.5	pF	$V_{G2S} = 4V, R_G = 470kW$
Reverse transfer capacitance	C_{rss}	—	0.025	0.05	pF	$f = 1MHz$
Power gain	PG1	28	32	—	dB	$V_{DS} = 5V, V_{G1} = 5V$ $V_{G2S} = 4V, R_G = 470kW$
Noise figure	NF1	—	1.0	1.6	dB	$f = 200MHz$
Power gain	PG2	12	16.5	—	dB	$V_{DS} = 5V, V_{G1} = 5V$ $V_{G2S} = 4V, R_G = 470kW$
Noise figure	NF2	—	2.85	3.7	dB	$f = 900MHz$

Main Characteristics

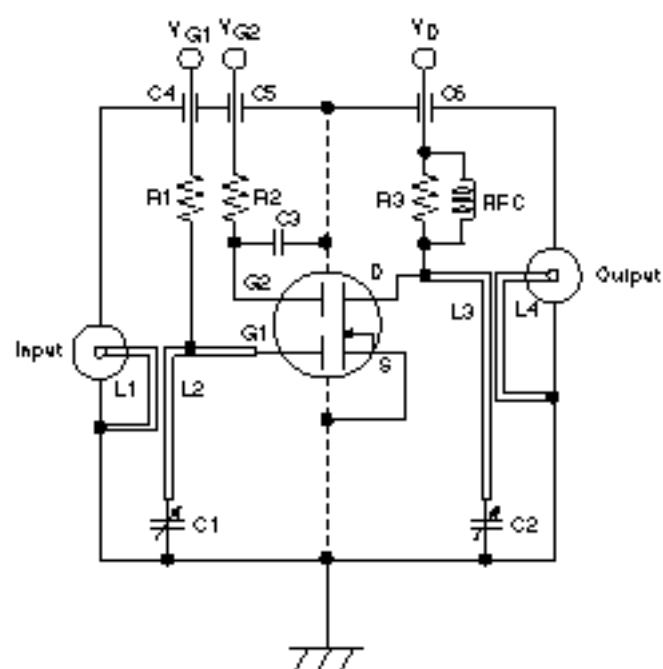
Test Circuit for Operating Items ($I_{D(on)}$, $|y_{fs}|$, C_{iss} , C_{oss} , C_{rss} , NF, PG)

Power Gain, Noise Figure Test Circuit



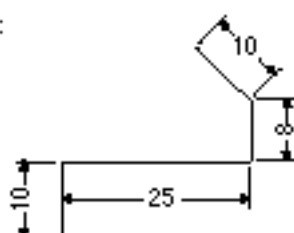
L1 : $\phi 1\text{mm}$ Enameled Copper Wire, inside dia. 10mm, 2Turns
 L2 : $\phi 1\text{mm}$ Enameled Copper Wire, inside dia. 10mm, 2Turns
 RFC : $\phi 1\text{mm}$ Enameled Copper Wire, inside dia. 5mm, 2Turns

900MHz Power Gain, Noise Test Circuit

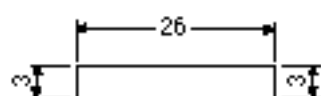


- C1, C2 : Variable Capacitor (10pF MAX)
 C3 : Disk Capacitor (1000pF)
 C4 to C6 : Air Capacitor (1000pF)
 R1 : 470 k Ω
 R2 : 47 k Ω
 R3 : 4.7 k Ω

L1 :

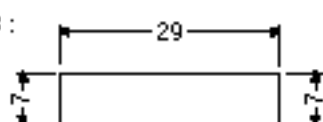


L2 :

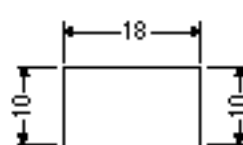


(ϕ 1mm Copper wire)
Unit : mm

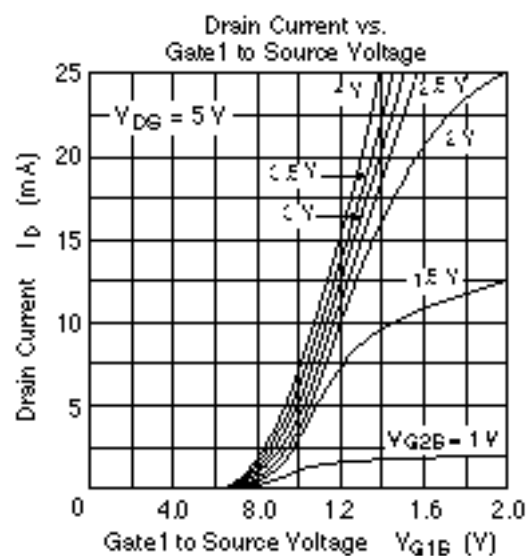
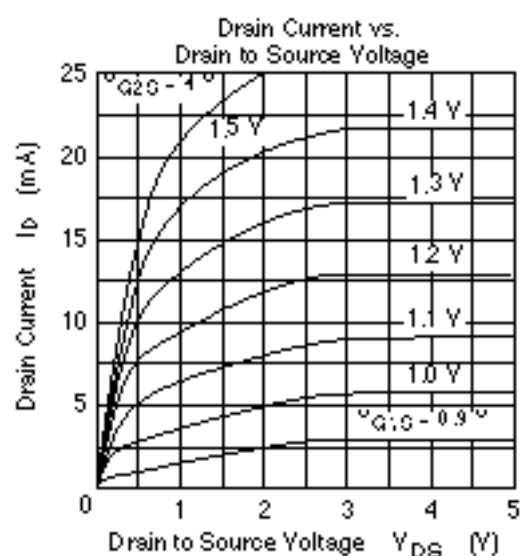
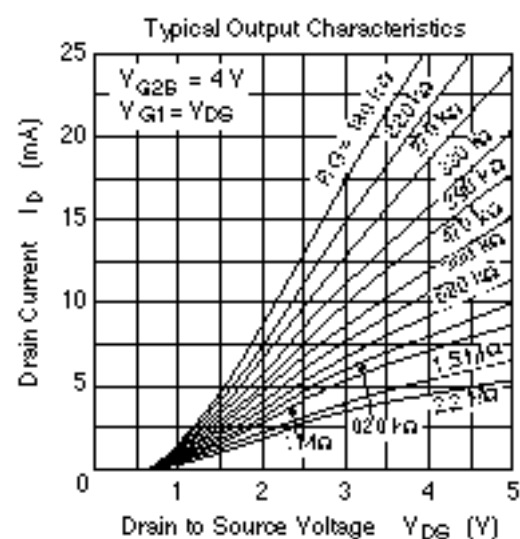
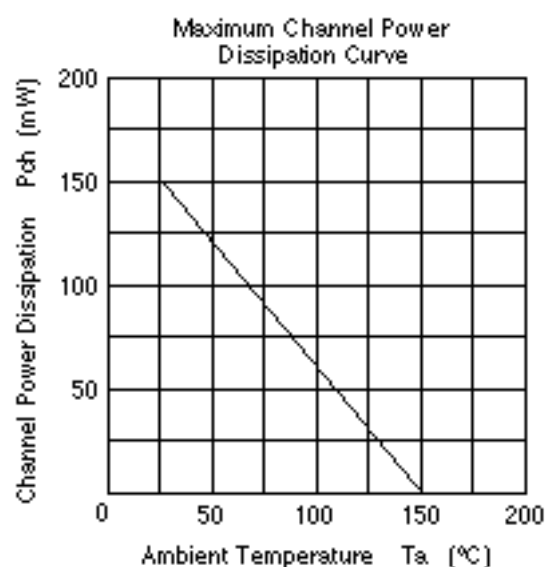
L3 :

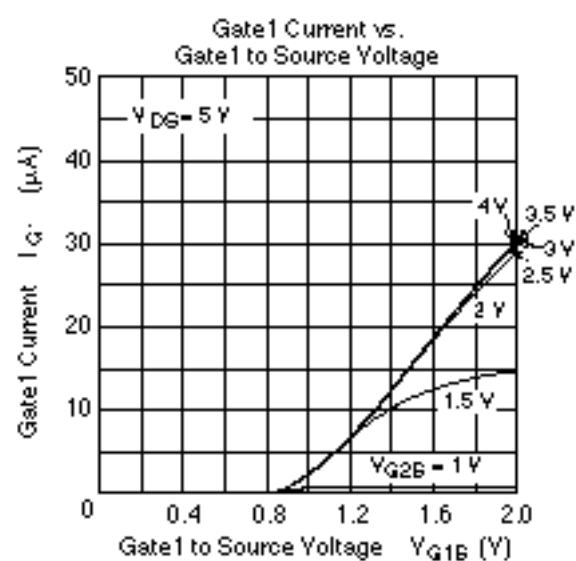
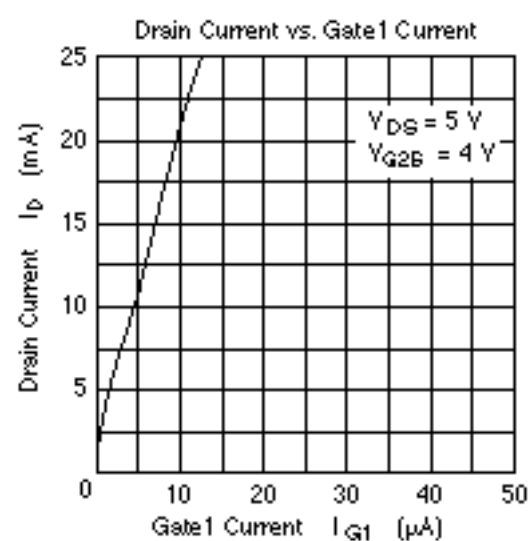
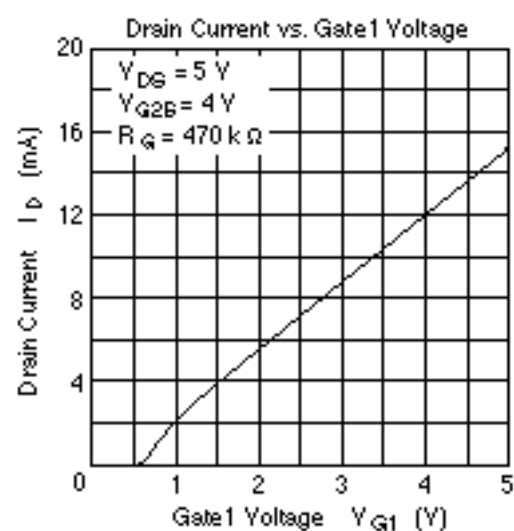
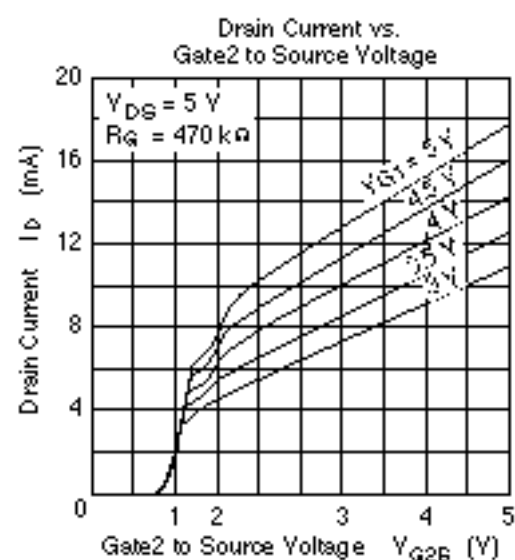


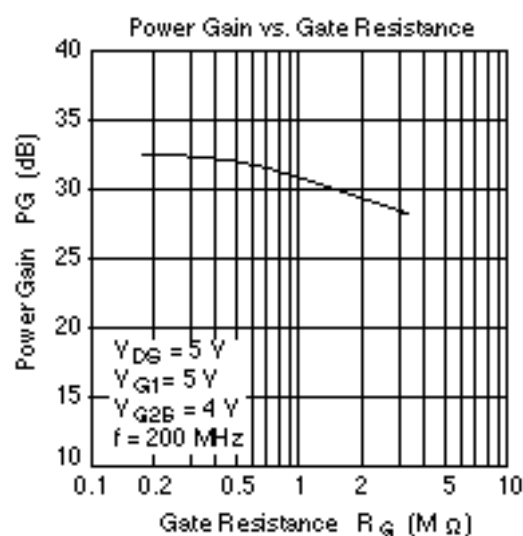
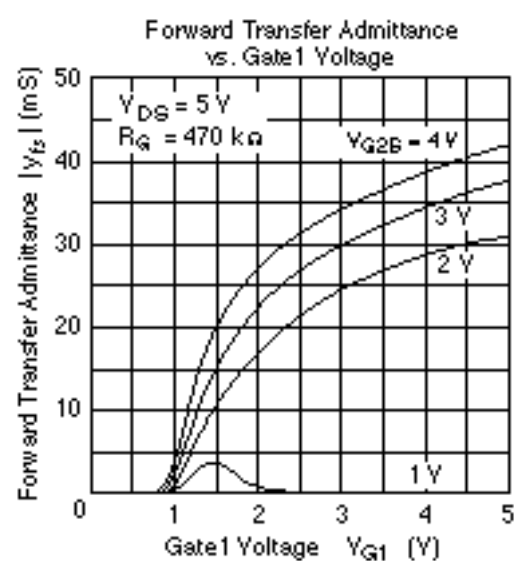
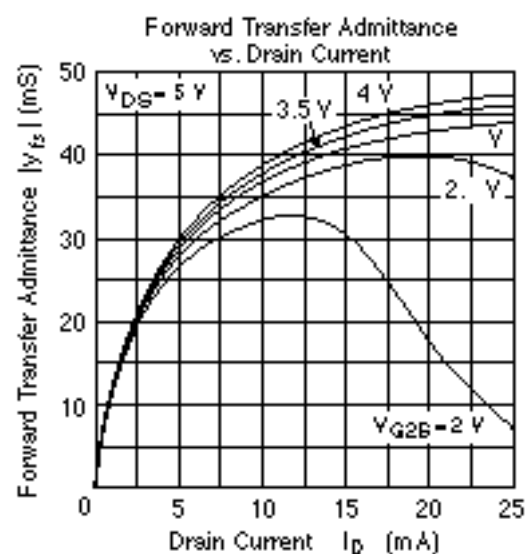
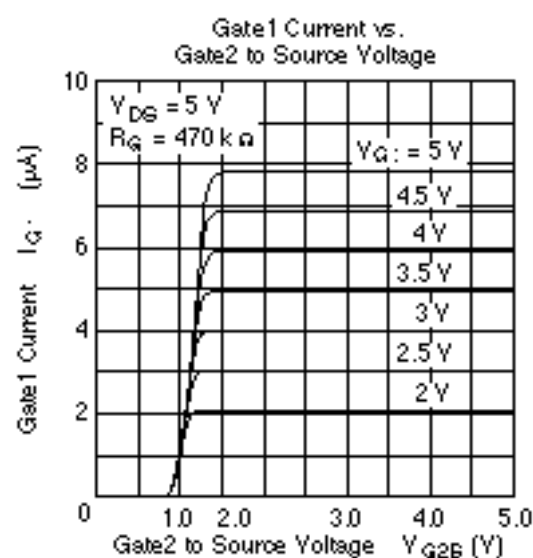
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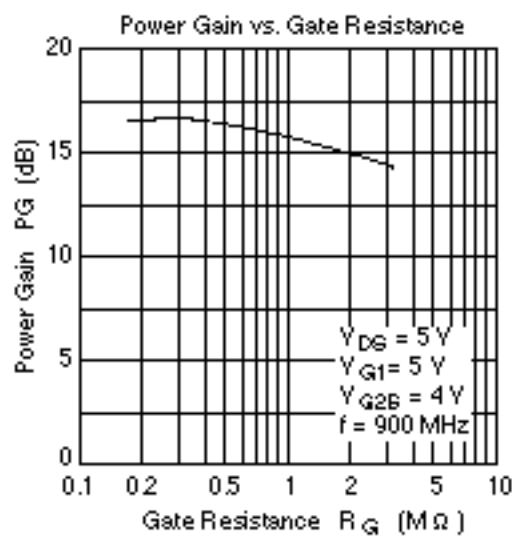
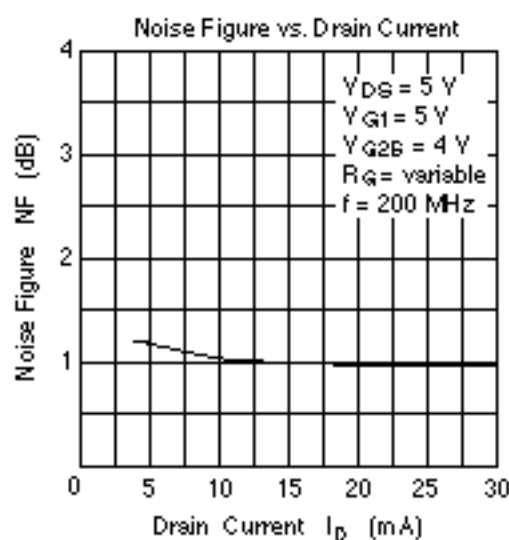
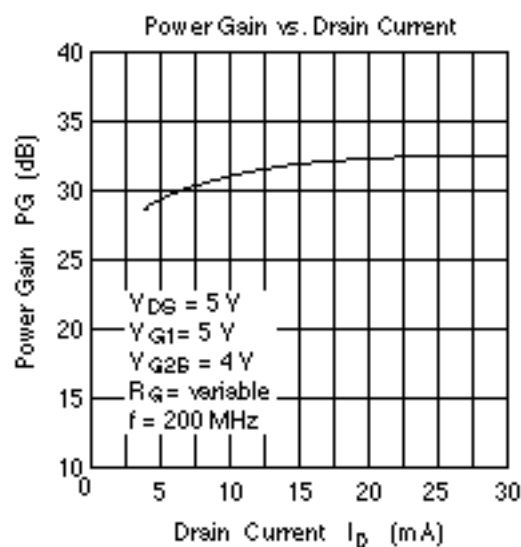
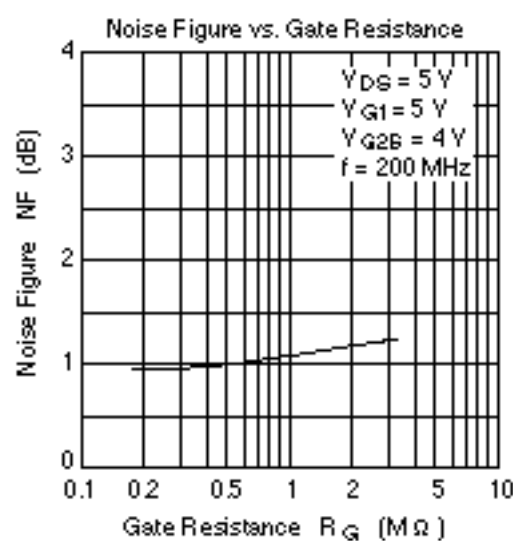


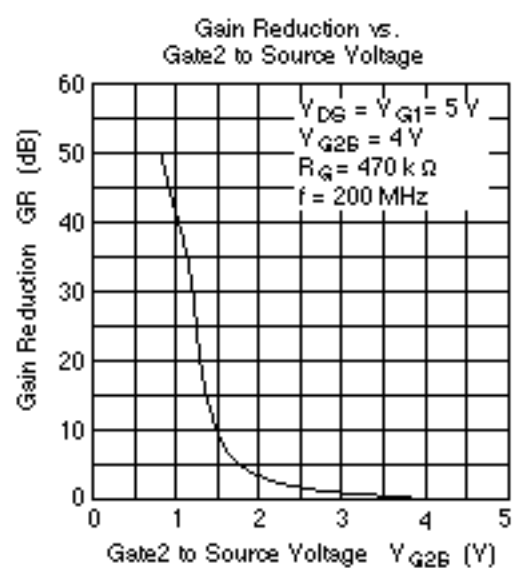
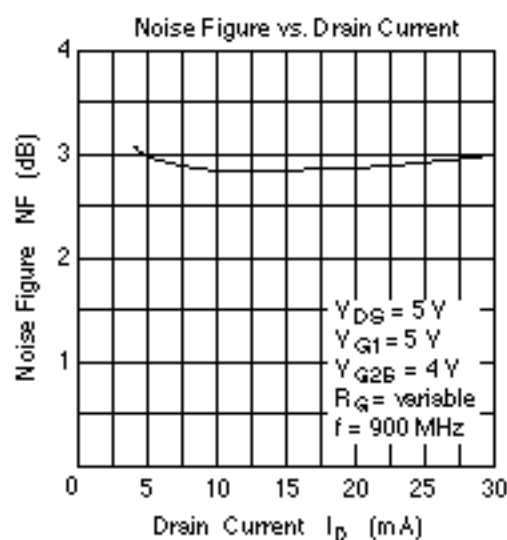
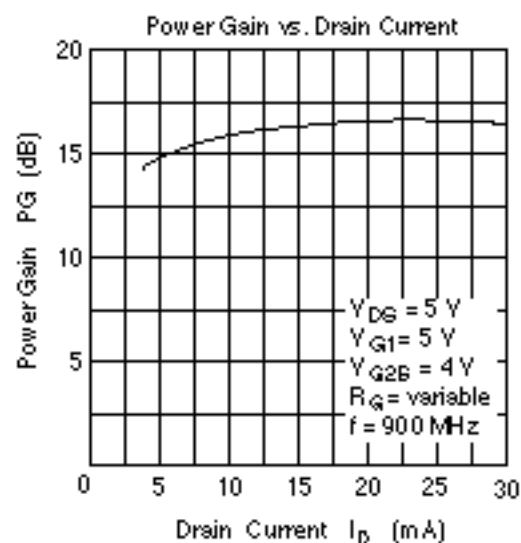
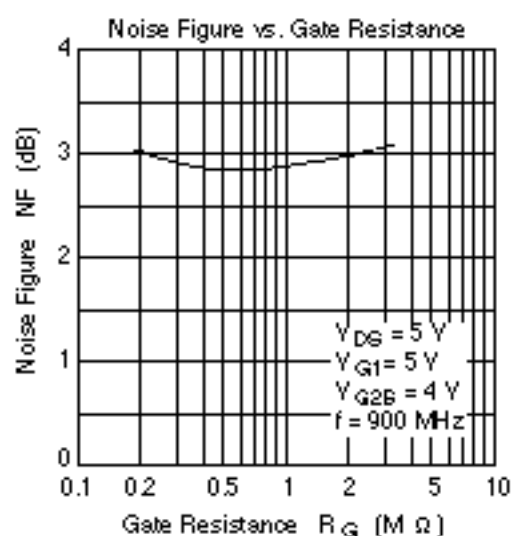
RFC : ϕ 1mm Copper wire with enamel 4turns inside dia. 6mm

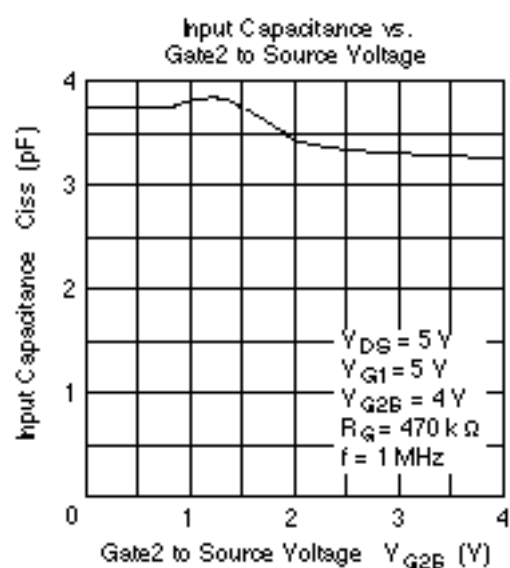
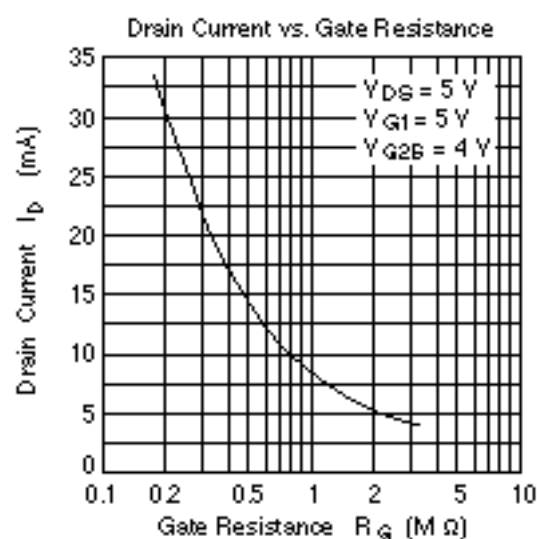
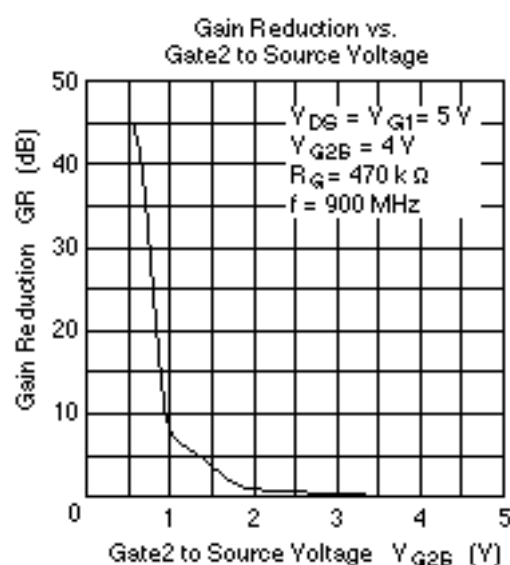




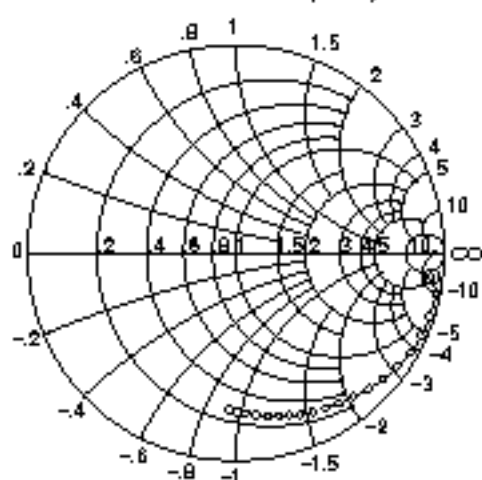








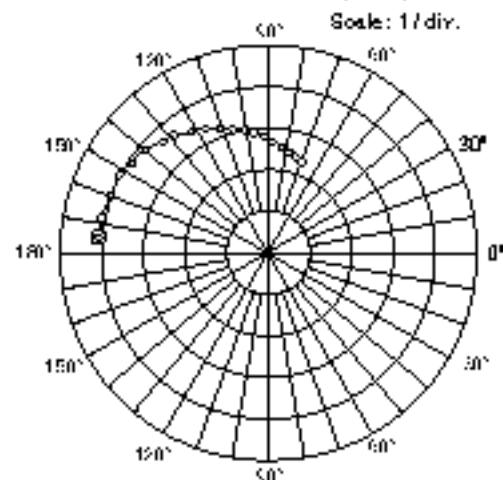
S11 Parameter vs. Frequency



Test Condition : $V_{DS} = 5\text{ V}$, $V_{G1} = 5\text{ V}$
 $V_{G2S} = 4\text{ V}$, $R_G = 470\text{ k}\Omega$
 $Z_0 = 50\ \Omega$
 50 to 1000 MHz (50 MHz step)

② →

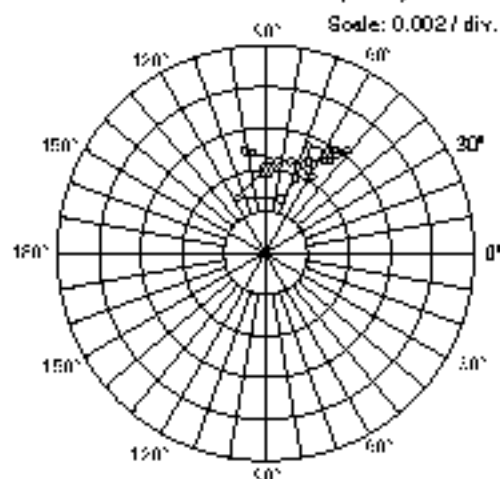
S21 Parameter vs. Frequency



Test Condition : $V_{DS} = 5\text{ V}$, $V_{G1} = 5\text{ V}$
 $V_{G2S} = 4\text{ V}$, $R_G = 470\text{ k}\Omega$
 $Z_0 = 50\ \Omega$
 50 to 1000 MHz (50 MHz step)

② →

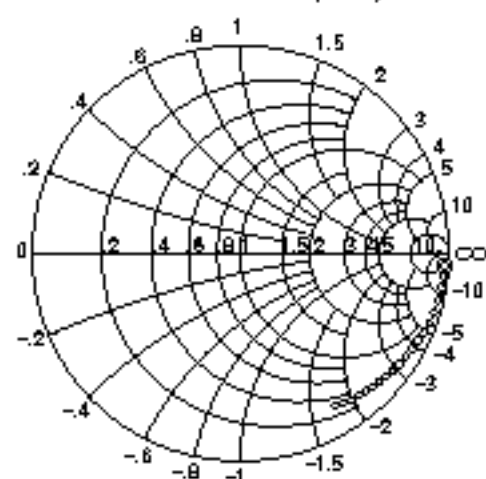
S12 Parameter vs. Frequency



Test Condition : $V_{DS} = 5\text{ V}$, $V_{G1} = 5\text{ V}$
 $V_{G2S} = 4\text{ V}$, $R_G = 470\text{ k}\Omega$
 $Z_0 = 50\ \Omega$
 50 to 1000 MHz (50 MHz step)

② →

S22 Parameter vs. Frequency



Test Condition : $V_{DS} = 5\text{ V}$, $V_{G1} = 5\text{ V}$
 $V_{G2S} = 4\text{ V}$, $R_G = 470\text{ k}\Omega$
 $Z_0 = 50\ \Omega$
 50 to 1000 MHz (50 MHz step)

② →

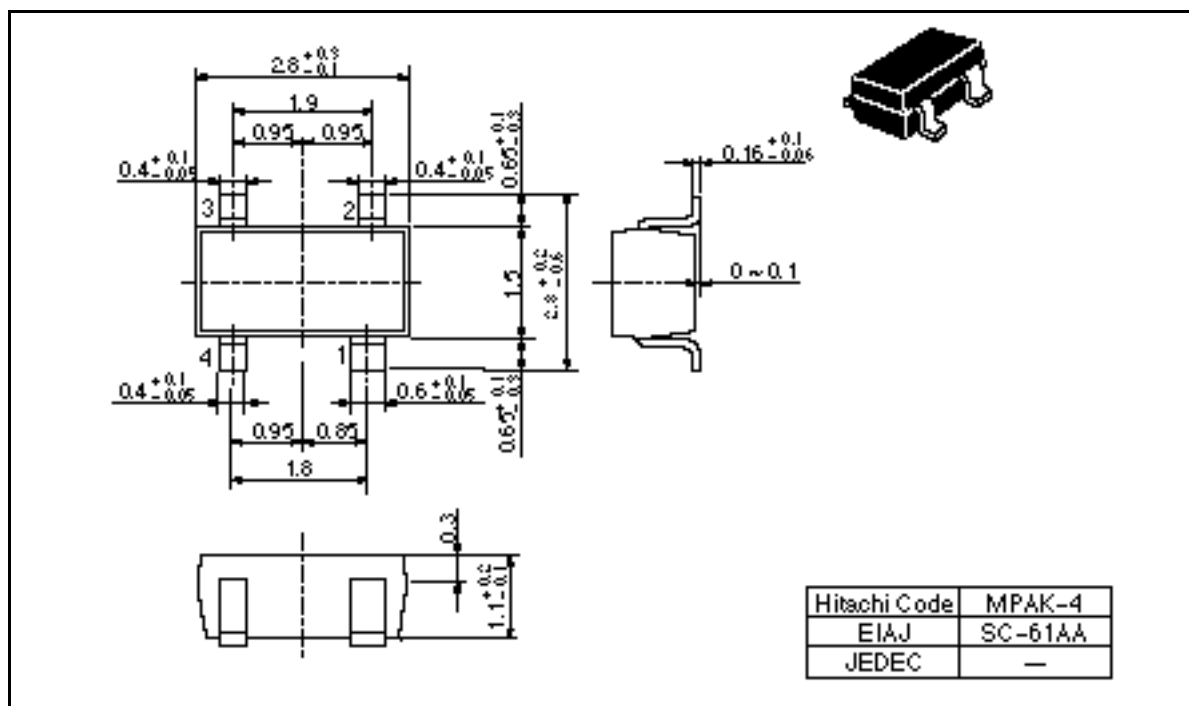
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Sparameter ($V_{DS} = V_{G1} = 5V$, $V_{G2S} = 4V$, $R_G = 470k\Omega$, $Z_0 = 50\Omega$)

f (MHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
50	0.947	-7.0	4.11	174.4	0.00400	89.0	0.985	-3.1
100	0.978	-11.9	4.13	167.1	0.00305	116.5	0.985	-6.8
150	0.973	-18.7	4.04	159.8	0.00266	75.5	0.982	-10.1
200	0.960	-23.8	4.01	152.7	0.00384	66.8	0.978	-13.5
250	0.956	-29.6	3.90	146.4	0.00453	70.1	0.970	-16.8
300	0.939	-35.5	3.85	139.9	0.00440	59.6	0.965	-20.0
350	0.930	-40.3	3.68	133.6	0.00550	67.2	0.957	-23.1
400	0.905	-45.7	3.63	128.3	0.00571	59.0	0.949	-26.2
450	0.889	-50.3	3.45	122.7	0.00583	54.2	0.940	-29.2
500	0.870	-55.6	3.35	116.6	0.00634	51.6	0.932	-32.1
550	0.855	-59.6	3.22	111.5	0.00596	56.2	0.924	-35.0
600	0.841	-63.9	3.10	106.3	0.00591	55.7	0.917	-37.7
650	0.826	-67.9	3.02	101.4	0.00544	54.9	0.908	-40.5
700	0.812	-71.8	2.89	96.1	0.00533	57.2	0.900	-43.1
750	0.799	-75.6	2.78	91.8	0.00495	64.6	0.893	-45.7
800	0.788	-78.9	2.70	87.5	0.00470	66.5	0.887	-48.1
850	0.778	-82.6	2.60	82.2	0.00460	75.1	0.880	-50.6
900	0.765	-85.8	2.48	78.1	0.00445	83.8	0.874	-52.9
950	0.763	-88.8	2.41	74.2	0.00486	97.0	0.869	-55.3
1000	0.748	-92.2	2.34	69.7	0.00502	102.6	0.864	-57.5

Package Dimensions

Unit: mm



Cautions

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